

JAR L L		IN TH	E UNITED STATES PAT	ENT A	AND TRADEM	IARK OFFICE	
In re A	spplication Shi et a	on of:	,	§ §	Group A	art Unit: Unknown er: Unknown	
Serial 1	No. 10/6	98,222		§ §	Atty. Dk	tt. No. 5589-06800	
Filed:		r 31, 20		\$\$\$\$\$\$\$\$\$\$\$\$\$\$\$	with the U.S. Post	ify that this correspondence is being deposited al Service as First Class Mail in an envelope	
For:			CT METHODS FOR ELECTRICAL	§ §		sistant Commissioner for Patents, Washington, date indicated below:	
			AND DETERMINING	§			
			ONTENT OF	§	3-19-04	Damala Drick	
	INSUL	ATING	FILMS	§ §	Date	Pamela Gerik	
			INFORMATION DISC	§ CLOSU	JRE STATEM	ENT	
	ant Comr ngton, D		r for Patents				
Sir:							
	Applica	ant requ	ests consideration of X th	e refei	rences listed or	n the attached Form PTO-1449	
and/or	the a	dditiona	l information identified belo	w in p	aragraph 3. A	copy of each reference listed on	
			enclosed.	•	3 F	,	
1.	This In	formatio	on Disclosure Statement is su	ıbmitte	d:		
	a.		within 3 months of the filing date of a national application other than a continued				
				of ent		al stage as set forth in § 1.491 in	
			an International application before the mailing date of a before the mailing of a t continued examination und	first C	ffice Action af	the merits; or ter the filing of a request for	
	b.		after the events of above paragraph 1a and prior to the mailing date of a final Office Action or Notice of Allowance, and thus: the certification of paragraph 2 below is provided, or a fee of \$180.00 is enclosed.				
	c.			e, and	thus: the certif	a Notice of Allowance and prior ication of paragraph 2 below is	

2.	It is h	It is hereby certified:					
		that each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the Statement, or					
		that no item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the person signing the certification after making reasonable inquiry, was known to any individual designated in § 1.56 (c) more than three months prior to the filing of the Statement.					
3.	\boxtimes	Consideration of the following additional information (including any co-pending or abandoned U.S. applications, prior uses and/or sales, etc.) is requested:					
		Serial No. 10/616,086 entitled METHODS AND SYSTEMS FOR DETERMINING A PROPERTY OF AN INSULATING FILM					
		Serial No. 10/677,445 entitled METHODS FOR NON-CONTACTING DIFFERENTIAL VOLTAGE MEASUREMENTS					
4.	For ea	For each non-English language reference listed on the attached Form PTO-1449:					
		reference is made to an English language translation submitted herewith, and/or					
		reference is made to a foreign patent office search report (in the English language) submitted herewith, and/or					
		reference is made to an English language translation of a foreign patent office search report submitted herewith, and/or					
		reference is made to the concise explanation contained in the specification of the present application at page(s), and/or					
		reference is made to the concise explanation set forth below:					
5.		Applicant also offers the following comments for the Examiner's consideration:					
6.		Also enclosed is a copy of a foreign search report citing these references.					
7.		The listed documents were brought to the attention of the Applicant(s) after payment of the issue fee in the captioned case. The documents were cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement. Applicant(s) request this Information Disclosure Statement and attached Form PTO-1449 be placed in the file of the captioned application.					
8.		Applicant(s) requests that the Information Disclosure Statement and attached Form PTO-1449 and references, which are being filed before the grant of the patent and pursuant to 37 C.F.R. § 1.97(i), be placed in the file of the captioned application.					

If any required fees are missing, the Commissioner is authorized to charge said fees to Conley Rose, P.C. Deposit Account No. 03-2769/5589-06800.

Respectfully submitted,

annapurapoherte

Ann Marie Mewherter Reg. No. 50,484

Agent for Applicant(s)

CONLEY ROSE, P.C. P. O. Box 684908 Austin, Texas 78768-4908 (512) 476-1400

Date: 3-19-04

Form PTO-1449 (modified) ATTY, DKT, NO. 5589-06800 SERIAL NO. 10/698,222 List of Patents and Publications APPLICANT: Shi et al. GROUP: Unknown For Applicant's Information Disclosure Statement FILING DATE: October 31, 2003 (Use several sheets if necessary) **U.S. PATENT DOCUMENTS DOCUMENT NUMBER** DATE FILING DATE IF EXAM. REF. NAME CLASS SUB APPROPRIATE **INITIALS** DES. **CLASS** SIPE MAR 2 2 2004 THADEMAR! FOREIGN PATENT DOCUMENTS **DOCUMENT NUMBER** TRANSLATION REF. DATE COUNTRY CLASS **SUB** EXAM. YES/NO **INITIALS CLASS** DES. 98/57358 1998-12-17 WO **A1** OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) Cosway et al., "Manufacturing Implementation of Corona Oxide Silicon (COS) Systems for Diffusion A2 Furnace Contamination Monitoring," 1997 IEEE/SEMI Advanced Semiconductor Manufacturing Conference, pp. 98-102. **A3** Miller, "A New Approach for Measuring Oxide Thickness," Semiconductor International, July 1995, pp. 147-148. Numerical Recipies in C, The Art of Scientific Computing, 2nd Ed., © Cambridge University Press A4 1988, 1992, p. 683, Weinberg, "Tunneling of Electrons from Si into Thermally Grown SiO₂," Solid-State Electronics. **A5** 1977, Vol. 20, pp. 11-18. **A6** Verkuil, "Rapid Contactless Method for Measuring Fixed Oxide Charge Associated with Silicon Processing," IBM Technical Disclosure Bulletin, Vol. 24, No. 6, 1981, pp. 3048-3053. **A7** "Contactless Photovoltage vs. Bias Method for Determining Flat-Band Voltage," IBM Technical Disclosure Bulletin, Vol. 32, Vol. 9A, 1990, pp. 14-17. **A8** "Contactless Electrical Equivalent Oxide Thickness Measurement," IBM Technical Disclosure Bulletin, Vol. 29, No. 10, 1987, pp. 4622-4623. Diebold et al., "Characterization and production metrology of thin transistor gate oxide films," **A9** Materials Science in Semiconductor Processing 2, 1999, pp. 103-147. Comizzoli, "Uses of Corona Discharges in the Semiconductor Industry," J. Electrochem. Soc., A10 1987, pp. 424-429. Weinzierl et al., "Non-Contact Corona-Based Process Control Measurements: Where We've Been, A11 Where We're Headed," Electrochemical Society Proceedings, Vol. 99-16, pp. 342-350. A12 Verkuil et al., "A Contactless Alternative to MOS Charge Measurements by Means of a Corona-Oxide-Semiconductor (COS) Technique," Electrochem. Soc. Extended Abstracts, 1988, Vol. 88-1, No. 169, pp. 261-262.

EXAMINER:

DATE CONSIDERED:

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the patent owner.